
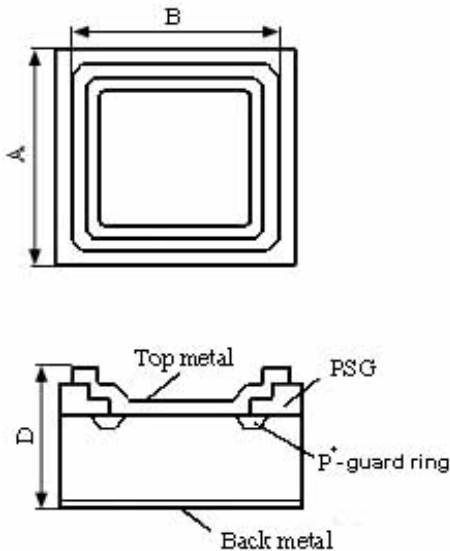


		3A/100V. Die Size-55mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort	
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	100	110	
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-	
DC Forward Voltage @ 25°C, $I_F=3,0\text{A}$ @ 25°C, $I_F=5,0\text{A}$	$V_F$	V	0,82 0,84	0,80 0,82	
Maximum Reverse Current @ 25°C, $V_R=100\text{V}$ @ 25°C, $V_R=110\text{V}$ @ 125°C, $V_R=100\text{V}$	$I_R$	mA	0,005 - 5,0	0,003 0,015 4,0	
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	80	-	
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<175^\circ\text{C}$ .	$I_{RRM}$	A	2,0		
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	$V_{ESD}$	kV	±8 (contact)		
Voltage Rate of Change	dV/dt	V/µS	10.000		
Operating Junction Temperature	$T_J$	°C	175		



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	1400 1400
$B_x$ $B_y$	Top Metal Size	1240 1240
D	Thickness	300max.
Scribe line Width		80

*Top metal:*  
a) **Al-Ni-Ag** – for Soldering;  
b) **Al** – for Wire Bonding.  
Backside metal: **Ti-Ni-Ag**.